

MA115

Silicon epitaxial planer type

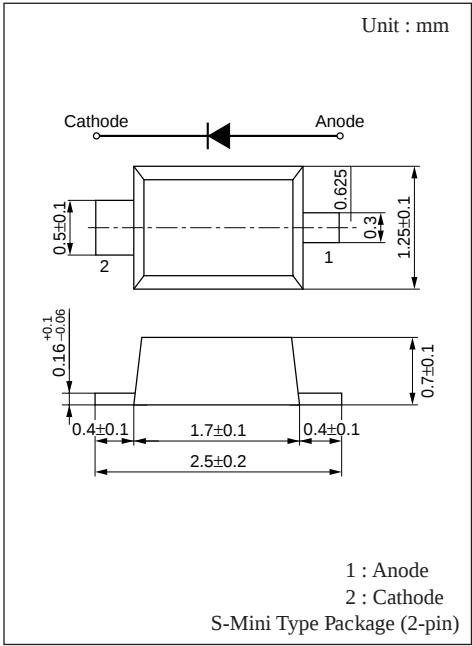
For small power rectification

- Features
 - Small S-Mini type package enabling high density mounting
 - High reverse voltage V_R

■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	200	V
Peak reverse voltage	V_{RM}	200	V
Output current	I_O	200	mA
Repetitive peak forward current	I_{FRM}	600	mA
Non-repetitive peak forward surge current	I_{FSM}^*	1	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	– 55 to +150	°C

* t=1s



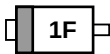
Marking Symbol : 1F

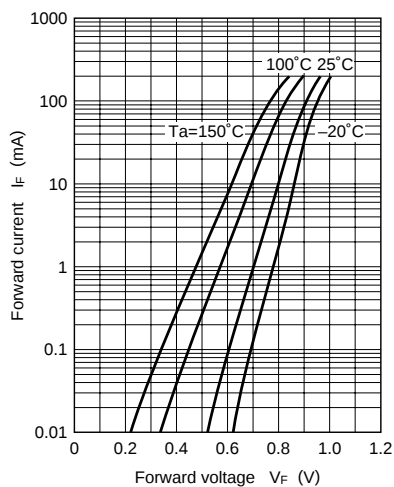
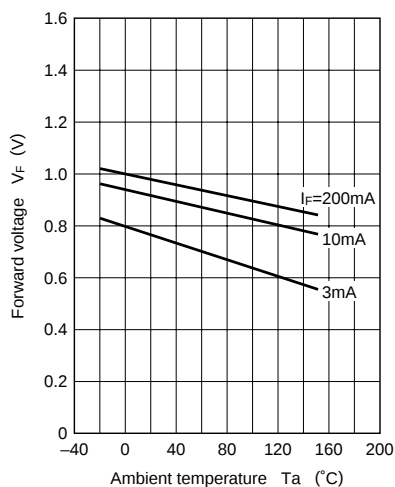
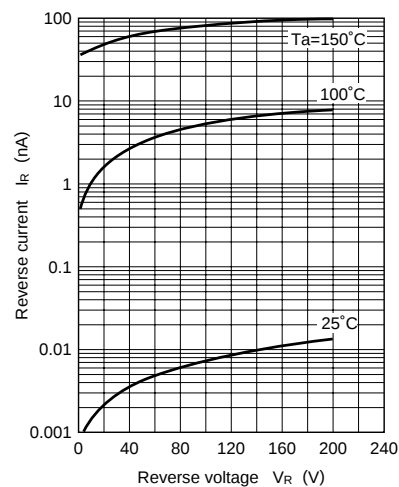
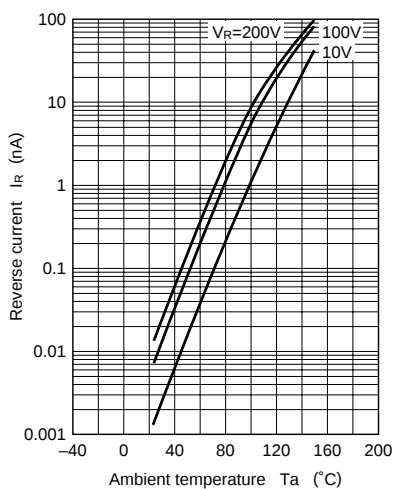
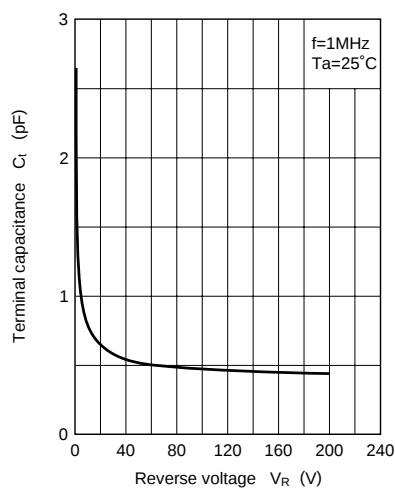
■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R=200V$			200	nA
Forward voltage (DC)	V_F	$I_F= 200mA$			1.2	V
Terminal capacitance	C_t	$V_R= 0V, f=1MHz$		4.5		pF

❖ Rated input/output frequency : 3MHz

■ Marking



$I_F - V_F$  $V_F - T_a$  $I_R - V_R$  $I_R - T_a$  $C_t - V_R$  $I_F(\text{surge}) - t_w$ 